2SJ271

P- Channel Silicon MOS FET
Very High-Speed Switching Applications

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Very high-speed switching.
- Low-voltage dreve.

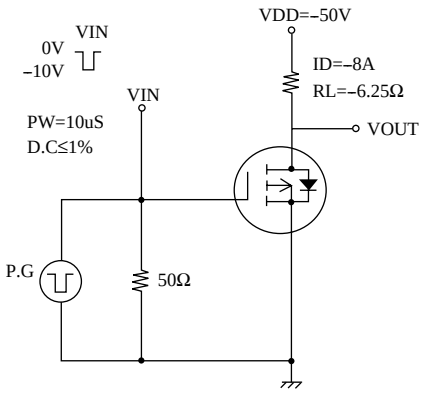
Absolute Maximum Ratings / Ta=25°C

				unit
Drain to Source Voltage	VDSS		−100	V
Gate to Source Voltage	VGSS		±15	V
Drain Current (D.C)	ID		−15	A
Drain Current (Pulse)	IDP	PW≤10μS, dutycycle≤1%	−60	A
Allowable power Dissipation	PD	Tc=25°C	70	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

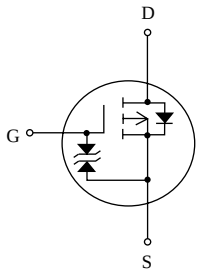
Electrical Characteristics / Ta=25°C

			min	typ	max	unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=−1mA , VGS=0	−100			V
Gate to Source Breakdown Voltage	V(BR)GSS	ID=±100μA , VGS=0	±15			V
Zero Gate Voltage Drain Current	IDSS	VDS=−100V , VGS=0			−100	μA
Gate to Source Leakage Current	IGSS	VGS=±12V , VDS=0			±10	μA
Cutoff Voltage	VGS(OFF)	VDS=−10V , ID=−1mA	−1.0		−2.0	V
Forward Transfer Admittance	| yfs |	VDS=−10V , ID=−8A	7.5	13		S
Static Drain to Source on State Resistance	RDS(On)1	ID=−8A , VGS=−10V		0.12	0.16	Ω
	RDS(On)1	ID=−8A , VGS=−4V		0.16	0.22	Ω
Input Capacitance	Ciss	VDS=−20V , f=1MHz		1900		pF
Output Capacitance	Coss	VDS=−20V , f=1MHz		400		pF
Reverse Transfer Capacitance	Crss	VDS=−20V , f=1MHz		80		pF
Turn-ON Delay Time	td(On)	See Specified Test Circuit .		18		ns
Rise Time	tr			25		ns
Turn-oFF Delay Time	td(Off)			300		ns
Fall Time	tf			120		ns
Diode Forward Voltage	VSD	IS =−15A , VGS = 0		−1.0	−1.5	V

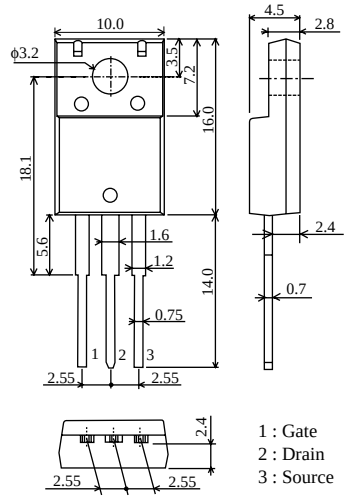
Switching Time Test Circuit



Elecrical Connection



Case Outline TO-220 (unit:mm)



1 : Gate
2 : Drain
3 : Source

Specifications and information herein are subject to change without notice.

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